

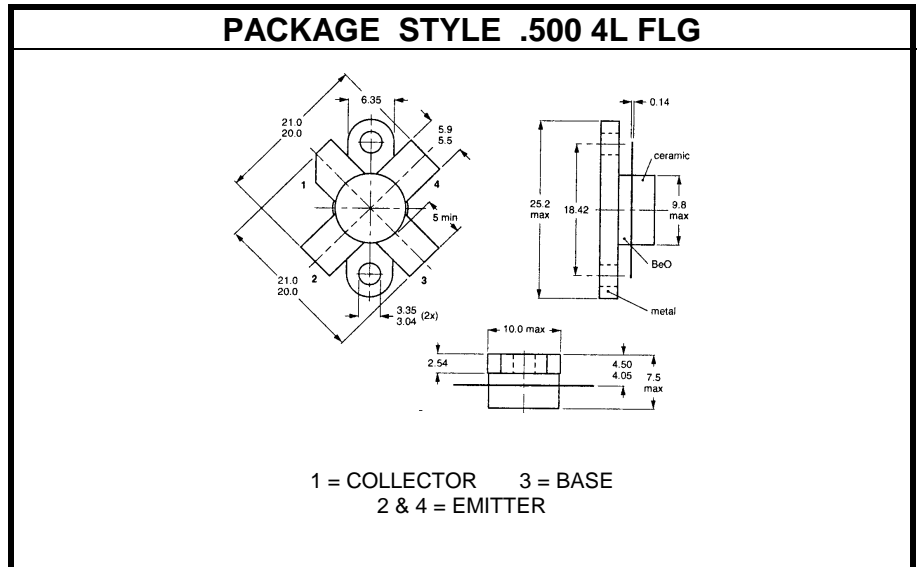
NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF422** is Designed for 2.0 MHz to 30 MHz, 28 V High Power Linear Amplifier Applications.

MAXIMUM RATINGS

I	20 A
V	40 V
P_{DISS}	290 W @ T _C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.6 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 200 mA	35			V
BV_{CES}	I _C = 100 mA	85			V
BV_{CBO}	I _C = 100 mA	85			V
BV_{EBO}	I _E = 10 mA	3.0			V
I_{CES}	V _{CE} = 28 V			20	mA
h_{FE}	V _{CE} = 5.0 V I _C = 5.0 A	10	30	120	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz		420		pF
P_{out}	V _{CE} = 28 V f = 30 MHz	150			W(PEP)
G_{PE}	V _{CC} = 28 V I _{CQ} = 150 mA P _{out} = 150 W (PEP)	10	13		dB
η	I _{C(max)} = 6.7 A f = 30 MHz		45		%
IMD			-33		dB